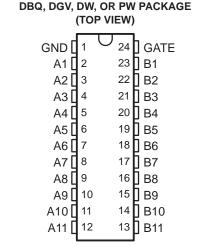
- Designed to be Used in Voltage-Limiting Applications
- 6.5-Ω On-State Connection Between Ports A and B
- Flow-Through Pinout for Ease of Printed Circuit Board Trace Routing
- Direct Interface With GTL+ Levels
- ESD Protection Exceeds JESD 22
 - 2000-V Human-Body Model (A114-A)
 - 1000-V Charged-Device Model (C101)

description/ordering information

The SN74TVC3010 provides 11 parallel NMOS pass transistors with a common gate. The low on-state resistance of the switch allows connections to be made with minimal propagation delay.



The device can be used as a 10-bit switch with the gates cascaded together to a reference transistor. The low-voltage side of each pass transistor is limited to a voltage set by the reference transistor. This is done to protect components with inputs that are sensitive to high-state voltage-level overshoots. (See Application Information in this data sheet.)

All of the transistors in the TVC array have the same electrical characteristics; therefore, any one of them can be used as the reference transistor. Since, within the device, the characteristics from transistor to transistor are equal, the maximum output high-state voltage (V_{OH}) is approximately the reference voltage (V_{REF}), with minimal deviation from one output to another. This is a large benefit of the TVC solution over discrete devices. Because the fabrication of the transistors is symmetrical, either port connection of each bit can be used as the low-voltage side, and the I/O signals are bidirectional through each FET.

ORDERING INFORMATION

TA	PACKAGE	<u></u> †	ORDERABLE PART NUMBER	TOP-SIDE MARKING	
	SOIC - DW	Tube SN74TVC3010DW		TVC3010	
	301C - DW	Tape and reel	SN74TVC3010DWR	1 1 1 0 3 0 1 0	
–40°C to 85°C	SSOP (QSOP) – DBQ	Tape and reel	SN74TVC3010DBQR	TVC3010	
	TSSOP – PW	Tape and reel	SN74TVC3010PWR	TT010	
	TVSOP – DGV	Tape and reel	SN74TVC3010DGVR	TT010	

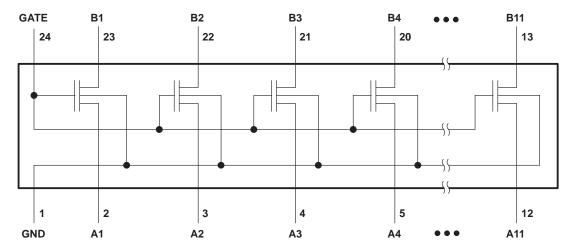
[†] Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



simplified schematic



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Input voltage range, V _I (see Note 1) Input/output voltage range, V _{I/O} (see Note 1)		 –0.5 V to 7 V
Continuous channel current		 128 mA
Input clamp current, I _{IK} (V _I < 0)		
Package thermal impedance, θ _{JA} (see Note 2):	: DBQ package	 61°C/W
	DGV package	 86°C/W
	DW package .	 46°C/W
	PW package	 88°C/W
Storage temperature range, T _{stg}		 –65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

recommended operating conditions

		MIN	TYP	MAX	UNIT
V _{I/O}	Input/output voltage	0		5	V
VGATE	GATE voltage	0		5	V
IPASS	Pass-transistor current		20	64	mA
TA	Operating free-air temperature	-40		85	°C



NOTES: 1. The input and input/output negative-voltage ratings may be exceeded if the input and input/output clamp-current ratings are observed.

^{2.} The package thermal impedance is calculated in accordance with JESD 51-7.

application operating conditions (see Figure 3)

		MIN	TYP	MAX	UNIT
VBIAS	BIAS voltage	V _{REF} + 0.6	2.1	5	V
VGATE	GATE voltage	V _{REF} + 0.6	2.1	5	V
VREF	Reference voltage	0	1.5	4.4	V
V _{DPU}	Drain pullup voltage	2.36	2.5	2.64	V
IPASS	Pass-transistor current		14		mA
IREF	Reference-transistor current		5		μΑ
TA	Operating free-air temperature	-40		85	°C

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	3	MIN	TYP [†]	MAX	UNIT
VIK	$V_{BIAS} = 0$,	$I_{I} = -18 \text{ mA}$				-1.2	V
V _{OL}	I _{REF} = 5 μA, V _{DPU} = 2.625 V,	$V_{REF} = 1.365 \text{ V},$ $R_{DPU} = 150 \Omega$	$V_S = 0.175 \text{ V},$ See Figure 1			350	mV
C _{i(GATE)}	V _I = 3 V or 0				24		pF
C _{io(off)}	V _O = 3 V or 0				4	12	pF
C _{io(on)}	V _O = 3 V or 0				12	30	pF
r _{on} ‡	I _{REF} = 5 μA, V _{DPU} = 2.625 V,	$V_{REF} = 1.365 V$, $R_{DPU} = 150 \Omega$	$V_S = 0.175 V$, See Figure 1			12.5	Ω

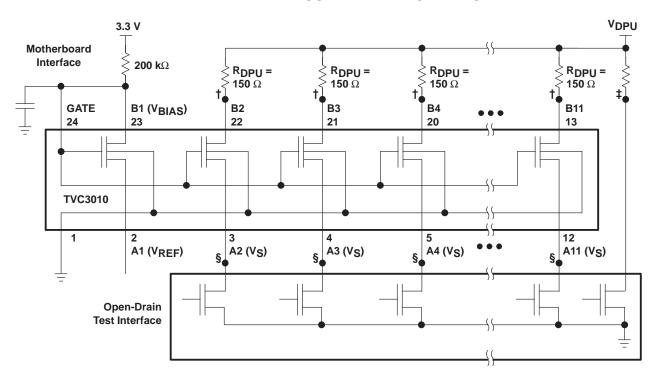
[†] All typical values are at $T_A = 25$ °C.

switching characteristics over recommended operating free-air temperature range, $V_{DPU} = 2.36 \text{ V}$ to 2.64 V (unless otherwise noted) (see Figure 1)

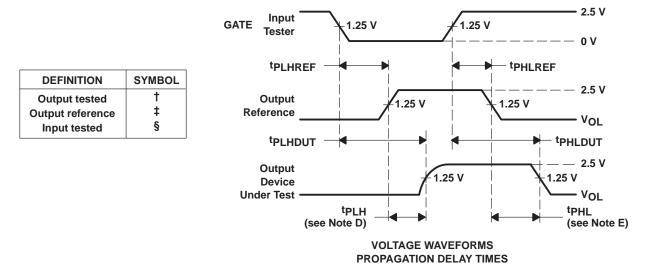
PARAMETER	FROM (INPUT)	TO (OUTPUT)	MIN	MAX	UNIT
tPLH	A or B	B or A	0	4	20
t _{PHL}	AUB	BULA	0	4	ns

[‡] Measured by the voltage drop between the A and B terminals at the indicated current through the switch. On-state resistance is determined by the lowest voltage of the two (A or B) terminals.

PARAMETER MEASUREMENT INFORMATION



TESTER CALIBRATION SETUP (see Note C)



- NOTES: A. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \ \Omega$, $t_f \leq 2 \ ns$.
 - B. The outputs are measured one at a time with one transition per measurement.
 - C. Test procedure: tpLHREF and tpHLREF are obtained by measuring the propagation delay of a reference measuring point. tPLHDUT and tPHLDUT are obtained by measuring the propagation delay of the device under test.

 - D. tplH = tplHDUT tplHREF E. tpHL = tpHLDUT tpHLREF

Figure 1. Tester Calibration Setup and Voltage Waveforms



TVC background information

In personal computer (PC) architecture, there are industry-accepted bus standards. These standards define, among other things, the I/O voltage levels at which the bus communicates. Examples include the GTL+ host bus, the AGP graphics port, and the PCI local bus. In new designs, the system components must communicate with existing bus infrastructure. Providing an evolutionary upgrade path is important in the design of PC architecture, but the existing bus standards must be preserved.

To achieve the ever-present need for smaller, faster, lighter devices that draw less power, yet have faster performance, most new high-performance digital integrated circuits are being designed and produced with advanced submicron semiconductor process technologies. These devices have thin gate-oxide or short channel lengths and very low absolute-maximum voltages that can be tolerated at the inputs/outputs (I/Os) without causing damage. In many cases, the I/Os of these devices are not tolerant of the high-state voltage levels on the preexisting buses with which they must communicate. Therefore, it became necessary to protect the I/Os of devices by limiting the I/O voltages.

The Texas Instruments (TI) translation voltage-clamp (TVC) family was designed specifically for protecting sensitive I/Os (see Figure 2). The information in this data sheet describes the I/O-protection application of the TVC family and should enable the design engineer to successfully implement an I/O-protection circuit utilizing the TI TVC solution.

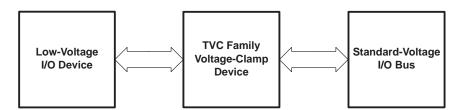
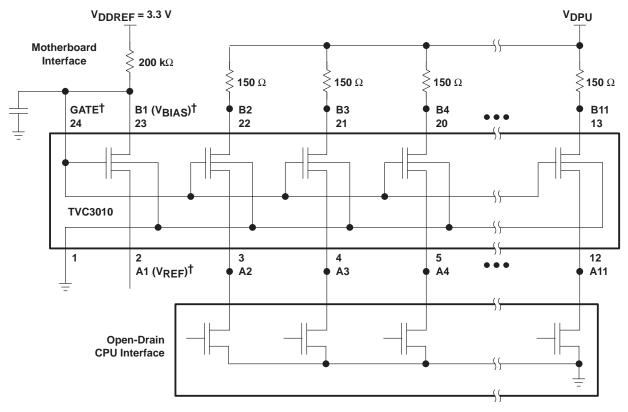


Figure 2. Thin Gate-Oxide Protection Application

TVC voltage-limiting application

For the voltage-limiting configuration, the common GATE input must be connected to one side (A or B) of any one of the transistors (see Figure 3). This connection determines the V_{BIAS} input of the reference transistor. The V_{BIAS} input is connected through a pullup resistor (typically, $200\,\mathrm{k}\Omega$) to the V_{DD} supply. A filter capacitor on V_{BIAS} is recommended. The opposite side of the reference transistor is used as the reference voltage (V_{REF}) connection. The V_{REF} input must be less than $V_{DDREF}-1$ V to bias the reference transistor into conduction. The reference transistor regulates the gate voltage (V_{GATE}) of all the pass transistors. V_{GATE} is determined by the characteristic gate-to-source voltage difference (V_{GS}) because $V_{GATE}=V_{REF}+V_{GS}$. The low-voltage side of the pass transistors has a high-level voltage limited to a maximum of $V_{GATE}-V_{GS}$, or V_{REF} .



[†] VREF and VBIAS can be applied to any one of the pass transistors. GATE must be connected externally to VBIAS.

Figure 3. Typical Application Circuit



electrical characteristics

The electrical characteristics of the NMOS transistors used in the TVC devices are illustrated by TI SPICE simulations. Figure 4 shows the test configuration for the TI SPICE simulations. The results, shown in Figures 5 and 6, show the current through a pass transistor versus the voltage at the source for different reference voltages. The plots of the dc characteristics clearly reveal that the device clamps at the desired reference voltage for the varying device environments.

Figure 5 shows the V-I characteristics, with low reference voltages and a reference-transistor drain-supply voltage of 3.3 V. To further investigate the spread of the V-I characteristic curves, V_{REF} was held at 2.5 V and I_{REF} was increased by raising V_{DDRFF} (see Figure 6). The result was a tighter grouping of the V-I curves.

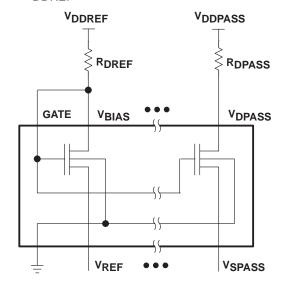


Figure 4. TI SPICE Simulation Schematic and Voltage-Node Names

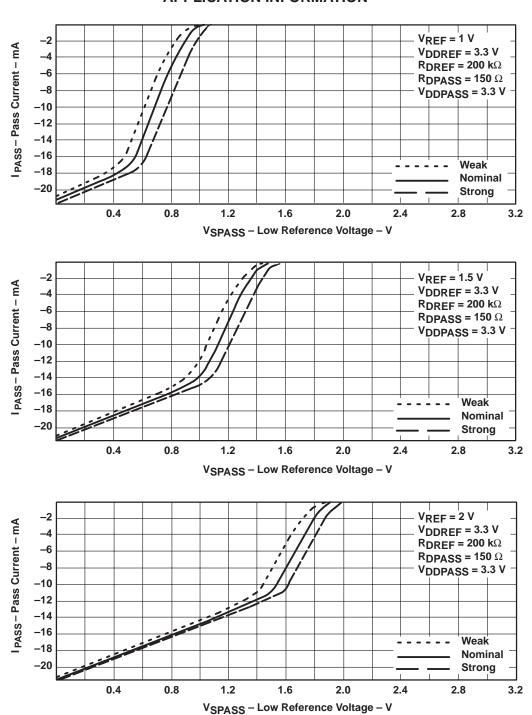


Figure 5. Electrical Characteristics at Low V_{REF} Voltages



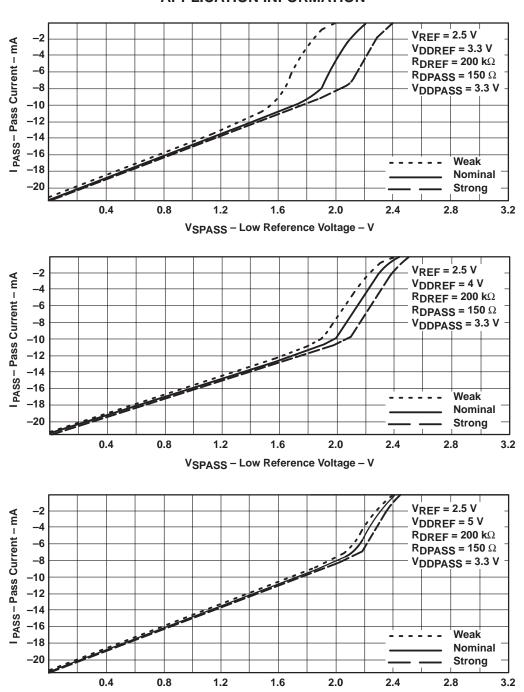


Figure 6. Electrical Characteristics at V_{REF} = 2.5 V

VSPASS - Low Reference Voltage - V



features and benefits

The TVC family has several features that benefit a system designer when implementing a sensitive-I/O-protection solution. Table 1 lists these features and their associated benefits.

Table 1. Features and Benefits

FEATURES	BENEFITS				
Any FET can be used as the reference transistor.	Ease of layout				
All FETs on one die, tight process control	Very low spread of VO relative to VREF				
No active control logic (passive device)	No logic power supply (V _{CC}) required				
Flow-through pinout	Ease of trace routing				
Devices offered in different bit-widths and packages	Optimizes design and cost effectiveness				
Designer flexibility with V _{REF} input	Allows migration to lower-voltage I/Os without board redesign				

conclusion

The TI TVC family provides the designer with a solution for protection of circuits with I/Os that are sensitive to high-state voltage-level overshoots. The flexibility of TVC enables a low-voltage migration path for advanced designs to align with industry standards.

frequently asked questions (FAQ)

- 1. Q: Can any of the transistors in the array be used as the reference transistor?
 - A: Yes, any transistor can be used as long as its V_{BIAS} pin is connected to the GATE pin.
- 2. Q: In the recommended operating conditions table of the data sheet, the typical V_{BIAS} is 3.3 V. Should V_{BIAS} be equal to or greater than V_{REF} on the reference transistor?
 - A: V_{BIAS} is a variable that is determined by V_{REF}. V_{BIAS} is connected to V_{DD} through a resistor to allow the bias voltage to be controlled by V_{REF}. V_{DD} can be as high as 5.5 V. V_{REF} needs to be at least 1 V less than V_{DDRFF} on the reference transistor.
- 3. Q: Do both A and B ports have 5-V I/O tolerance or is 5-V I/O tolerance provided only on the low-voltage side?
 - A: Both ports are 5-V tolerant.



16-Aug-2012

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/ Ball Finish	MSL Peak Temp ⁽³⁾	Samples (Requires Login)
SN74TVC3010DBQR	ACTIVE	SSOP	DBQ	24	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	
SN74TVC3010DBQRE4	ACTIVE	SSOP	DBQ	24	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	
SN74TVC3010DBQRG4	ACTIVE	SSOP	DBQ	24	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	
SN74TVC3010DGVR	ACTIVE	TVSOP	DGV	24	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
SN74TVC3010DGVRE4	ACTIVE	TVSOP	DGV	24	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
SN74TVC3010DGVRG4	ACTIVE	TVSOP	DGV	24	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
SN74TVC3010DW	ACTIVE	SOIC	DW	24	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
SN74TVC3010DWE4	ACTIVE	SOIC	DW	24	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
SN74TVC3010DWG4	ACTIVE	SOIC	DW	24	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
SN74TVC3010DWR	ACTIVE	SOIC	DW	24	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
SN74TVC3010DWRE4	ACTIVE	SOIC	DW	24	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
SN74TVC3010DWRG4	ACTIVE	SOIC	DW	24	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
SN74TVC3010PW	ACTIVE	TSSOP	PW	24	60	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
SN74TVC3010PWE4	ACTIVE	TSSOP	PW	24	60	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
SN74TVC3010PWG4	ACTIVE	TSSOP	PW	24	60	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
SN74TVC3010PWR	ACTIVE	TSSOP	PW	24	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
SN74TVC3010PWRE4	ACTIVE	TSSOP	PW	24	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	



PACKAGE OPTION ADDENDUM

16-Aug-2012

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/ Ball Finish	MSL Peak Temp ⁽³⁾	Samples (Requires Login)
SN74TVC3010PWRG4	ACTIVE	TSSOP	PW	24	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

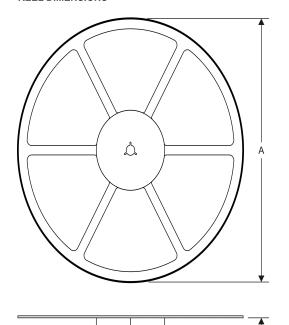
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

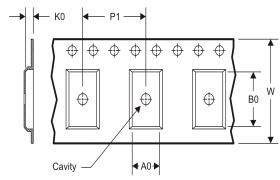
www.ti.com 16-Aug-2012

TAPE AND REEL INFORMATION

REEL DIMENSIONS







A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

TAPE AND REEL INFORMATION

*All dimensions are nominal

All ullilerisions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74TVC3010DBQR	SSOP	DBQ	24	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN74TVC3010DGVR	TVSOP	DGV	24	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74TVC3010DWR	SOIC	DW	24	2000	330.0	24.4	10.75	15.7	2.7	12.0	24.0	Q1
SN74TVC3010PWR	TSSOP	PW	24	2000	330.0	16.4	6.95	8.3	1.6	8.0	16.0	Q1

www.ti.com 16-Aug-2012



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74TVC3010DBQR	SSOP	DBQ	24	2500	367.0	367.0	38.0
SN74TVC3010DGVR	TVSOP	DGV	24	2000	367.0	367.0	35.0
SN74TVC3010DWR	SOIC	DW	24	2000	367.0	367.0	45.0
SN74TVC3010PWR	TSSOP	PW	24	2000	367.0	367.0	38.0

DGV (R-PDSO-G**)

24 PINS SHOWN

PLASTIC SMALL-OUTLINE



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15 per side.

D. Falls within JEDEC: 24/48 Pins – MO-153 14/16/20/56 Pins – MO-194 DW (R-PDSO-G24)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
- D. Falls within JEDEC MS-013 variation AD.



DBQ (R-PDSO-G24)

PLASTIC SMALL-OUTLINE PACKAGE

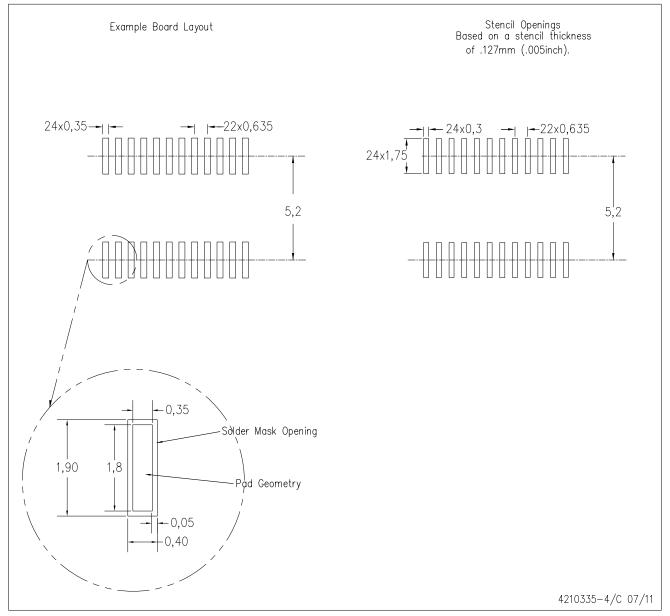


- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15) per side.
- D. Falls within JEDEC MO-137 variation AE.



DBQ (R-PDSO-G24)

PLASTIC SMALL OUTLINE PACKAGE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.



PW (R-PDSO-G24)

PLASTIC SMALL OUTLINE

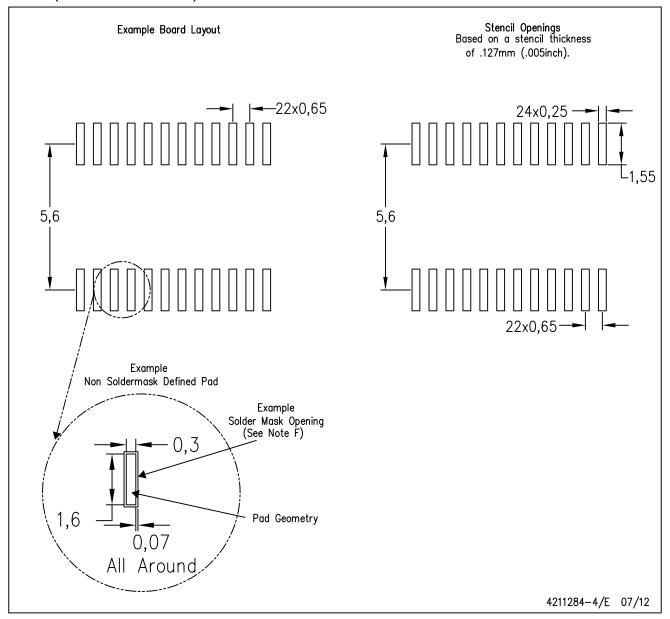


- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO-153



PW (R-PDSO-G24)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate design.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, enhancements, improvements and other changes to its semiconductor products and services per JESD46C and to discontinue any product or service per JESD48B. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All semiconductor products (also referred to herein as "components") are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its components to the specifications applicable at the time of sale, in accordance with the warranty in TI's terms and conditions of sale of semiconductor products. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by applicable law, testing of all parameters of each component is not necessarily performed.

TI assumes no liability for applications assistance or the design of Buyers' products. Buyers are responsible for their products and applications using TI components. To minimize the risks associated with Buyers' products and applications, Buyers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI components or services are used. Information published by TI regarding third-party products or services does not constitute a license to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of significant portions of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI components or services with statements different from or beyond the parameters stated by TI for that component or service voids all express and any implied warranties for the associated TI component or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Buyer acknowledges and agrees that it is solely responsible for compliance with all legal, regulatory and safety-related requirements concerning its products, and any use of TI components in its applications, notwithstanding any applications-related information or support that may be provided by TI. Buyer represents and agrees that it has all the necessary expertise to create and implement safeguards which anticipate dangerous consequences of failures, monitor failures and their consequences, lessen the likelihood of failures that might cause harm and take appropriate remedial actions. Buyer will fully indemnify TI and its representatives against any damages arising out of the use of any TI components in safety-critical applications.

In some cases, TI components may be promoted specifically to facilitate safety-related applications. With such components, TI's goal is to help enable customers to design and create their own end-product solutions that meet applicable functional safety standards and requirements. Nonetheless, such components are subject to these terms.

No TI components are authorized for use in FDA Class III (or similar life-critical medical equipment) unless authorized officers of the parties have executed a special agreement specifically governing such use.

Only those TI components which TI has specifically designated as military grade or "enhanced plastic" are designed and intended for use in military/aerospace applications or environments. Buyer acknowledges and agrees that any military or aerospace use of TI components which have *not* been so designated is solely at the Buyer's risk, and that Buyer is solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI has specifically designated certain components which meet ISO/TS16949 requirements, mainly for automotive use. Components which have not been so designated are neither designed nor intended for automotive use; and TI will not be responsible for any failure of such components to meet such requirements.

roducts		Applications
udia	ununu ti com/ou dio	Automotive on

Audio Automotive and Transportation www.ti.com/automotive www.ti.com/audio www.ti.com/communications **Amplifiers** amplifier.ti.com Communications and Telecom **Data Converters** dataconverter.ti.com Computers and Peripherals www.ti.com/computers **DLP® Products** Consumer Electronics www.ti.com/consumer-apps www.dlp.com DSP dsp.ti.com **Energy and Lighting** www.ti.com/energy Clocks and Timers www.ti.com/clocks Industrial www.ti.com/industrial Interface interface.ti.com Medical www.ti.com/medical Logic logic.ti.com Security www.ti.com/security

Power Mgmt power.ti.com Space, Avionics and Defense www.ti.com/space-avionics-defense

Microcontrollers microcontroller.ti.com Video and Imaging www.ti.com/video

OMAP Mobile Processors www.ti.com/omap TI E2E Community e2e.ti.com

Wireless Connectivity www.ti.com/wirelessconnectivity

www.ti-rfid.com

Pr